

VHF variable capacitance diode

FEATURES

- Excellent linearity
- Ultra small plastic SMD package
- C28: 1 pF; ratio: 14.

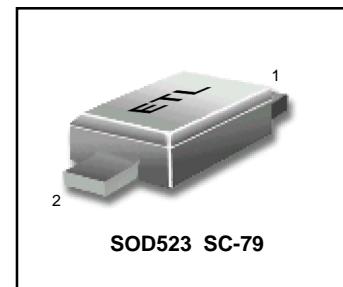
APPLICATIONS

- Electronic tuning in satellite tuners
- Tuneable coupling
- Voltage controlled oscillators (VCO).

DESCRIPTION

The BB181 is a variable capacitance diode, fabricated in planar technology and encapsulated in the SOD523 (SC-79) ultra small plastic SMD package.

BB 181



LIMITING VALUES in accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_R	continuous reverse voltage	–	30	V
I_F	continuous forward current	–	20	mA
T_{stg}	storage temperature	– 55	+150	°C
T_j	operating junction temperature	– 55	+150	°C

ELECTRICAL CHARACTERISTICS $T_j = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_R	reverse current	$V_R = 30 \text{ V}$; see Fig.2	–	10	nA
		$V_R = 30 \text{ V}$; $T_j = 85^\circ\text{C}$; see Fig.2	–	200	nA
r_s	diode series resistance	$f = 470 \text{ MHz}$; note 1	–	3	Ω
C_d	diode capacitance	$V_R = 0.5 \text{ V}$; $f = 1 \text{ MHz}$; see Figs 1 and 3	8	17	pF
		$V_R = 28 \text{ V}$; $f = 1 \text{ MHz}$; see Figs 1 and 3	0.7	1.055	pF
$\frac{C_{d(0.5V)}}{C_{d(28V)}}$	capacitance ratio	$f = 1 \text{ MHz}$	12	16	

Note

1. V_R is the value at which $C_d = 9 \text{ pF}$.

SEMICONDUCTOR

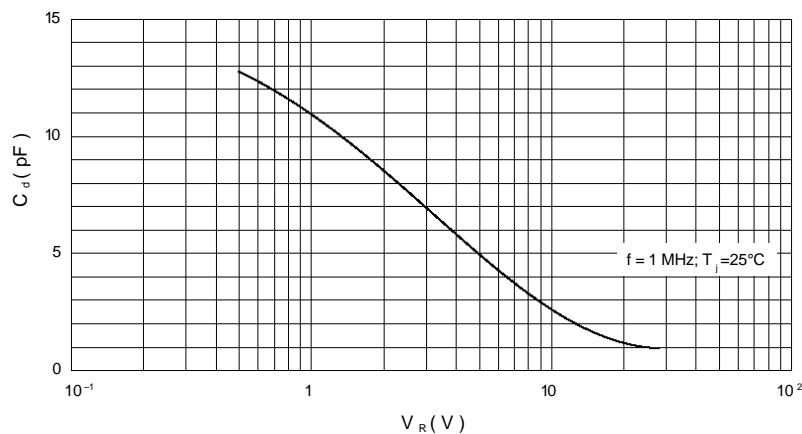
BB 181


Fig.1 Diode capacitance as a function of reverse voltage; typical values.

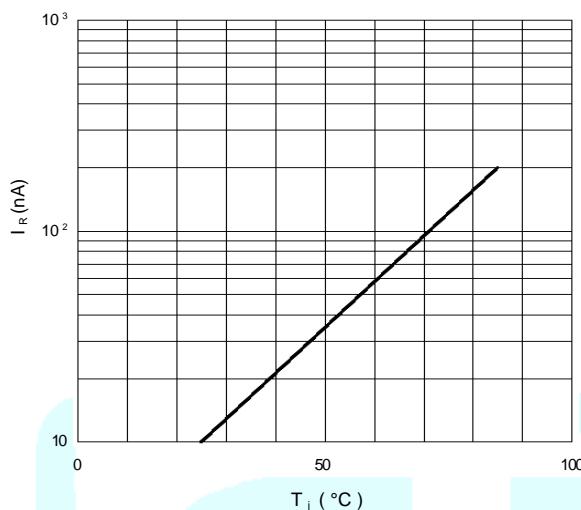


Fig.2 Reverse current as a function of junction temperature; maximum values.

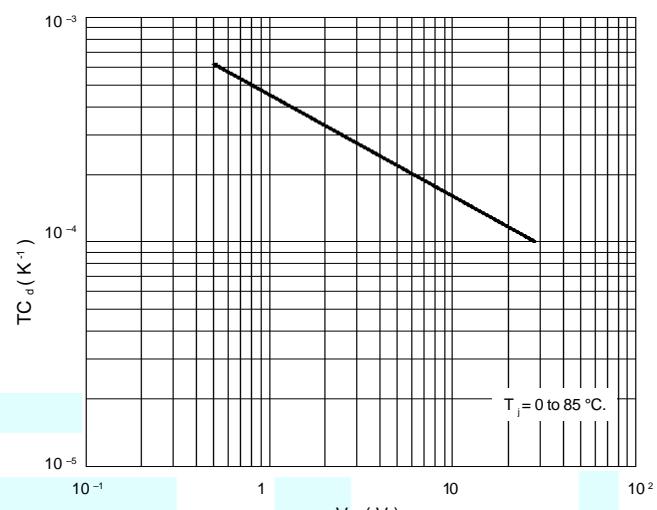


Fig.3 Temperature coefficient of diode capacitance as a function of reverse voltage; typical values.

SEMICONDUCTOR